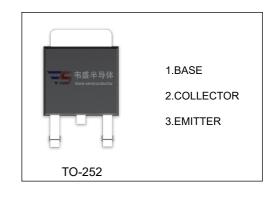


2SD1802 TRANSISTOR (NPN)

FEATURES

- Adoption of FBET,MBIT Processes
- Large Current Capacity and Wide ASO
- Low Collector-to-Emitter Saturation Voltage
- Fast Switching Speed



MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	50	V
V _{EBO}	Emitter-Base Voltage	6	V
Ic	Collector Current –Continuous	3	А
Pc	Collector Power Dissipation	1	W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55-150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =10 △ A, I _E =0	60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =10⊠A, I _C =0	6			V
Collector cut-off current	I _{CBO}	V _{CB} =40V, I _E =0			1	⊠ A
Emitter cut-off current	I _{EBO}	V _{EB} =4V, I _C =0			1	⊠ A
DC current gain	h _{FE(1)}	V _{CE} =2V, I _C =100mA	100		560	
DC current gain	h _{FE(2)}	$V_{CE}=2V$, $I_{C}=3A$	35			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =2A, I _B =100mA			0.5	٧
Base-emitter saturation voltage	V _{BE(sat)}	I _C =2A, I _B =100mA			1.2	V
Transition frequency	f _T	V _{CE} =10V, I _C =50mA		150		MHz
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz		25		pF

CLASSIFICATION OF h_{FE(1)}

Rank	R	S	Т	U
Range	100-200	140-280	200-400	280-560



